

1. _____ converts weak signal into strong signal. :->amplifier
2. _____ can be converted into an instrument to measure voltage, current and resistance for both AC and DC applications :->Moving Magnetic coil
3. _____ converts sinusoidal signal to unidirectional flow and not pure D.C :->Rectifier
4. _____ is a circuit which offers low resistance to the current in one direction and high resistance in the opposite direction. :->Rectifier
5. _____ is the disadvantage of Half Wave Rectifier. :->High Ripple Factor
6. A hole is the vacancy created when: :->An electron breaks its covalent band
7. A N-type semiconductor impurities are: :->tetravalent
8. A P-N junction diode's dynamic conductance is directly proportional to :->the current
9. A PNP diode: :->is always made of silicon
10. A p-type semiconductor impurities are :->pentavalent
11. A p-type semiconductor is having _____ impurities: :->boron
12. A p-type semiconductor is having _____ impurities: :->boron
13. A transistor has _____ PN junctions. :->two
14. A weak signal applied in the input circuit of transistor appears in the amplified form in the _____ circuit. :->Collector
15. Accumulation of electron at fluorescent screen causes :->Will repel the electron beam.
16. Accuracy of a Digital Instruments is _____ :->Difference between actual value and **measured value**
17. After firing an SCR, if the gate pulse is removed, the SCR current: :->remain the same
18. Ammeter is used to measure _____ :->Current only
19. An n-type semiconductor is having _____ impurities: :->silicon
20. An n-type semiconductor is having _____ impurities: :->silicon
21. An SCR is a _____ switch. :->unidirectional
22. Any voltage that is connected across a P-N junction is called _____ voltage. :->Bias
23. BJT is a _____ terminal semi-conductor switching device. :->3
24. Bridge Rectifier consists of _____ number of diodes :->Four
25. Defluxion factor of CRT is :->Inverse of sensitivit y
26. Defluxion sensitivity is defined as the ratio of :->Deflection on screen and applied voltage on **defluxion on plates**
27. Digital voltmeters use _____ for display :->A/D converters
28. Electric instruments are used in _____ applications :->High voltage measurement
29. Electro static defluxion system used in _____ applications :->Both Television CRT and Low
- Frequency applications**
30. Electron gun in C.R.T consists of _____ components :->Heated cathode, Focusing anode, **control grid and accelerating electrodes**
31. Electron vacancy distribution of an Si atom is :->2, 8, 4
32. Electronic indicating meters work on the principle of :->Motor principle and its current responding **device**
33. Electronic instruments are used in _____ applications :->Very sensitive voltage **measurement**
34. Energy required to break a covalent in a semiconductor is: :->Equal to the width of the forbidden **energy gap**
35. Expand BJT :->Bi Polar Junction Transistor
36. Expand C.R.O :->Cathode Ray Oscilloscope
37. Expand C.R.T :->Cathode Ray Tube
38. Extrinsic semiconductor means :->Pure semiconductor without any impurities
39. For a silicon diode, the value of the forward-bias voltage typically :->must be greater than 0.7 V
40. For active region operation of a NPN transistor: :->Emitter is negative with respect to base
41. For active region operation of a PNP transistor: :->Emitter is positive with respect to base
42. Full scale range of a Digital Instruments is _____ :->Difference between actual value and **measured value**
43. Full Wave Rectifier consists of _____ number of diodes :->Two
44. Generally used small signal amplifier transistors are: :->NPN silicon transistor in plastic packages
45. Germanium atom contains: :->Four valence electrons

46. Grid Bias Control is a use to :->Brightness variation
47. Half Wave Rectifier consists of _____ number of diodes :->One
48. If emitter current in a transistor is 1 mA, then collector current I_c is nearly _____ :->1 mA
49. If negative potential on control grid of CRT is increased, the intensity of Of spot is _____ :->decreased
50. If the firing angle in an SCR rectifier is increased, output is _____ :->decreased
51. If the supply voltage exceeds the breakover voltage of SCR, then SCR is _____ :->destroyed
52. In _____ C.R.O is used applications :->Visual observation, Measurement and Analysis
53. In a BJT , with $a =$ _____ :->
54. In a BJT , with $a = 0.98$, equals : :->49
55. In a BJT , with $a = 100$, a equals: :->0.99
56. In a common base connection, current amplification factor is 0.9. If the emitter current is 1 mA, then collector current I_c is _____ :->0.9 mA
57. In a common base connection, current amplification factor is 0.9. If the emitter current is 1 mA, then collector current I_c is _____ :->0.9mA
58. In a common base connection, $I_c = 0.95\text{mA}$ and $I_B = 0.05\text{mA}$. The value of a is _____ :->0.95
59. In a common base connection, $I_E = 1 \text{ mA}$, $I_c = 0.95\text{mA}$. Then the Value of I_B is _____ :->0.05mA
60. In a common base connection, $I_E = 1 \text{ mA}$, $I_c = 0.95\text{mA}$. Then the Value of I_B is _____ :->0.05mA
61. In a forward biased PN diode, the injected hole current in the n-region I_s is proportional to: _____ (if Q is the total stored charge) :-> Q
62. In a full-wave rectifier , if a.c supply frequency is 50hz , then a.c. ripple in The output is _____ :->100hz
63. In a half wave rectifier , maximum value of current , I_m is 189, then Root mean square value(I_{rms}) value is _____ :->94.5 mA
64. In a PN diode ,hole diffuse from p-region to n-region because: :->there is higher concentration of **holes in the p-region**
65. In a PN diode, with the increase of reverse bias, the reverse current: :->remains constant
66. In a PN junction in N-type semiconductor bar _____ , _____ exists :->Electrons ,donor **ions**
67. In a PN junction in P-type semiconductor bar _____ , _____ exists :->Holes, acceptor ions
68. In a PN-Junction junction region consists of :->Depletion region
69. In a PNP transistor operating in the active region, in the base region, the main stream of current is : :->diffusion of holes
70. In a PNP diode, breakover condition is marked by a sudden _____ in current. :->increased
71. In a transistor , a reverse-biased collector base junction has _____ Resistance path. :->high
72. In a transistor , the forward-biased emitter-base junction has a _____ Resistance path. :->low
73. In a transistor , the main function of _____ is to supply majority Charge carriers(either electrons or holes) to the base and hence It is more heavily doped. :->Emitter
74. In a transistor the collector region width is _____ than emitter region width. :->larger
75. In a transistor, currentflow in :->base and collector leads
76. In a transistor, the main function of _____ is to collect majority Charge carriers through the base. This is moderately doped. :->Collector
77. In active region o peratio n of a transistor : :->Emitter junction is forward biased while collector **junction is reverse biased**
78. In an NPN transistor oper ating in the active region the main current Crossing the co llector junction fro m base side is: :->Electron diffusion current
79. In an NPN transistor, the function of the emitter is: :->To inject electrons into the base
80. In an unbiased PN junction , the junction current at equilibrium is: :->zero due to equal and opposite **currents crossing the junction**
81. In C.R.T electron travels in fo llowing path :->Electron gun**Defluxion coils**
Fluo rescent screen

82. In C.R.T Function of electron gun is to :->Single electron beam with high velocity
83. In C.R.T Horizontal deflection plates causes :->Horizontal defluxion on screen
84. In C.R.T Vertical deflection plates causes :->Vertical defluxion on screen
85. In case of a transistor which the following equation is correct :->
86. In CRT, the arrangement of electrodes which produce a focused beam of electrons is called the _____
_____ :->Electron gun
87. In cutoff region operation of a transistor Where JC means collector junction JE means emitter junction :->Both JE and JC are reverse biased
88. In dual beam CRO no of beams are :->2
89. In dual beam CRO no of electron gun are :->2
90. In dual trace CRO no of beams are :->2
91. In dual trace CRO no of electron gun are :->1
92. In electro static C.R.T in case of defluxion sensitivity which of the following are true :->Defluxion **sensitivity independent of defluxion voltage**
93. In electro static C.R.T in case of defluxion which of the following are false :->Defluxion Directly **proportional to square defluxion voltage**
94. In electro static C.R.T in case of velocity of electron which of the following are true :->Velocity of **electron is directly proportional to square root anode voltage**
95. In Electro static defluxion system defluxion will be in :->Parabolic path
96. In Electro static defluxion system sweep voltage should be applied to the _____ :->Horizontal **plates.**
97. In Fluorescent screen _____ element is generally used. :->Phosphor
98. In Full Wave Rectifier , maximum possible rectifier efficiency is _____ :->81.2 %
99. In Ge diode , the cutin voltage is about: :->0.2 volt
100. In Half Wave Rectifier , maximum possible rectifier efficiency is _____ :->40.6 %
101. In Half Wave Rectifier , Root mean square value(:-> $I_m / 2$) value is _____
102. In magneto static C.R.T in case of defluxion sensitivity which of the following are true :->Defluxion sensitivity independent of magnetic field
103. In magneto static C.R.T in case of defluxion which of the following are false :->Defluxion **directly proportional to square root of magnetic field**
104. In Magneto static defluxion system defluxion will be in :->Circular path
105. In Magneto static defluxion system defluxion will be in :->Perpendicular to the path of **electron**
106. In Moving coil the current needed to deflect the pointer all the way to the way to the last mark of calibration scale is called of _____ :->Full scale defluxion current
107. In n-type semiconductor :->electrons form the majority carriers
108. In pn junction depletion region formed by recombination of _____ , _____ :->electrons , holes
109. In p-type semiconducto r: :->free electrons from the minority carriers
110. In saturation reg ion operation of a transistor Where JC means collector junction JE mea ns e mit ter junction :->Both JE and JC are forward biased
111. In SCR the breakover vo ltage with the increase of positive gate current :->increased
112. In SCR, the turn - off time :->Increase with increase of T
113. In Si diode , the cutin voltage is about: :->0.6 volt
114. In the comparison of electro static and Magneto static defluxion system which of the following is true :->Electro static defluxion system used at high frequencies
115. In the comparison of electro static and Magneto static defluxion system which of the following is true :->Electro static defluxion system consumes low power
116. In the comparison of electro static and Magneto static defluxion system consumes high power because :->Electro static defluxion system operates for lees time
117. In the moving coil type indicator, indicator is connected to a spring because :->The spring **provides restoring torque**
118. In which of the following instruments amplification is used :->Electronic measurements

instruments

119. Intrinsic semiconductor means :->Pure semiconductor without any impurities
120. Junction breakdown occurs :->under reverse bias
121. LISSAJOUS figures pattern are used in _____ measurement :->Phase difference

measurement

122. LISSAJOUS figures pattern generated when :->when two signals are applied to horizontal and vertical plates simultaneously
123. Magneto static deflexion system used in _____ applications :->Television CRT
124. Moving coil is used to detect _____ :->Magnetic Flux
125. Moving Magnetic coil can be converted into an AC audio frequency ammeter by connecting _____ :->Rectifier
126. Multimeter used to measure _____ :->Current, Voltage and Resistance
127. Ohmic contacts are used in a PN junction to :->Connect terminal directly
128. Ohm-meter is used to measure _____ :->Resistance only
129. One of application of P-N junction diode is _____ :->Rectifier
130. Peak Inverse Voltage of a Full Wave Rectifier is _____ :->2 Vm
131. Peak Inverse Voltage of a Half Wave Rectifier is _____ :->Vm
132. P-N junction diode acts as a _____ in forward and reverse bias conditions. :->Switch
133. P-N junction diode is also used in _____ circuits :->clipping
134. P-N junction diode is also used in _____ circuits :->clamping
135. Resolution of a Digital Instruments is _____ :->Least voltage Change Value that can

be measured

136. SCR consists _____ number of PN junctions. :->3
137. SCR is a _____ terminal semi-conductor switching device. :->3
138. SCR is a four layer device with one _____ :->Gate
139. SCR is also called as _____ :->Thyristor
140. SCR uses: :->one gate on the p-layer next to cathode
141. Semiconductor materials have _____ bonds. :->covalent
142. Spot of beam deflexion by applying voltage on the vertical and horizontal deflexion plates is called :->Electro static deflexion
143. Sweep voltage generator also called _____ :->Time base generator
144. The 3 terminals of BJT are _____ :->Base, Emitter, Collector
145. The 3 terminals of SCR are _____ :->Base, Emitter, Gate
146. The advantage of Bridge Rectifier is _____ is not required. :->centre tapped

transformer

147. The anode of SCR is always maintained at _____ potential With respect to cathode. :->positive
148. The area within a semiconductor diode where no mobile current carriers exist when it is forward biased is called _____ region. :->depletion
149. The bridge rectifier produces a voltage output nearly _____ that of Centre-tap circuit for a given transformer. :->twice
150. The emitter is _____ doped. :->heavily
151. The forward bias on PN junction :->both holes on the p-side and electrons on n-side cross the **junction to the opposite sides.**
152. The function of a transistor is to do _____ :->amplification
153. The input impedance of a CRO is :->The impedance offered by the CRO to the signal
154. The most widely used semiconducting material in electronic devices is :->silicon
155. The most widely used transistor circuit arrangement is _____ circuit. :->CE
156. The No load Voltage in the case of Half Wave Rectifier is _____ :->
157. The normal way to close an SCR is by appropriate _____ :->Gate current
158. The Ratio of Rectification in Full Wave Rectifier is _____ :->
159. The Ratio of Rectification P_{dc} / P_{ac} in Half Wave Rectifier is _____ :->0.406
160. The reverse bias on PN junction: :->pushes the electrons and holes away from the junction
161. The Ripple Factor of Bridge Rectifier is _____ :->0.482

162. The Ripple Factor of Full Wave Rectifier is _____ :->0.482
163. The Ripple Factor of Half Wave Rectifier is _____ :->1.21
164. The SCR is often employed as a _____ controlled switch. :->Gate
165. The term bias means :->a dc voltage applied across the P-N junction to control its operation.
166. The Transformer Utilization Factor of Bridge Rectifier is :->0.812
167. The Transformer Utilization Factor of Full Wave Rectifier is :->0.693
168. The Transformer Utilization Factor of Half Wave Rectifier is :->0.287
169. The Value of α is always less than _____ :->unity
170. The width of depletion layer of a P-N junction :->is increased under reverse bias.
171. Time base sweep generator gives _____ wave form. :->sawtooth wave
172. To obtain a stable display of the signal on screen on CRT screen sweep signal applied must be :->Synchronous with the signal
173. To open the SCR(i.e to make it non-conducting), we have to Reduce the supply voltage to _____ :->0
174. Transducer is used to _____ :->Convert Non-electric signal to electric signal
175. Transformer is _____ in a full wave rectifier. :->essential
176. Units of defluxion is :->Centimeter
177. Units of Forbidden gap in semiconductors is :->ev
178. Voltmeter is used to measure _____ :->Voltage only
179. We use _____ in Bias Stabilization circuits. :->P-N junction diode
180. When a diode forward biased :->conducts current
181. When a layer of N type material is sandwiched between two layers of P- type material, the transistor is known as _____ transistor. :->PNP
182. When a layer of P type material is sandwiched between two layers of N- type material, the transistor is known as _____ transistor. :->NPN
183. When a P-N junction is formed, diffusion current causes :->Barrier potential
184. When a P-N junction is forward biased :->the current is produced by both holes and **electrons**.
185. When large Resistance is connected to a Moving coil in series it acts as :->Voltmeter
186. When small Resistance is connected to a Moving coil in shunt it acts as :->Ammeter
187. When two signal are applied to horizontal and vertical plates simultaneously with phase difference $\theta = 00$ then LISSAJOUS figure reduces to :->Straight line with 450 slope
188. When two signal are applied to horizontal and vertical plates simultaneously with phase difference $\theta = 900$ then LISSAJOUS figure reduces to :->CIRCLE
189. When two signal are applied to horizontal and vertical plates simultaneously with phase difference $\theta = 1800$ then LISSAJOUS figure reduces to :->Straight line with -1 slope
190. Which of the following are components of Electronic measurement instruments :->Transducer, **Signal amplifier, Indicating meter**
191. Which of the following are properties of Digital Instruments :->Greater resolution, Better **Accuracy, Easy readability.**
192. Which of the following are properties of Electronic measurements instruments? :->Higher **sensitivity , Faster Response ,greater flexibility**
193. Which of the following is a component of CRO? :->Sweep generator
194. Which of the following is not a component of C.R.T :->Sweep generator
195. Which of the following is not component of CRO? :->Electron gun
196. Which of the following wave is applied to CRO as sweep generator? :->Sawtooth wave
197. $\alpha = a / \text{_____} :->1 - a$

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